3.3 V 16-bit buffer/driver; 3-state Rev. 08 — 22 March 2010

Product data sheet

1. General description

The 74LVT16244B; 74LVTH16244B is a high-performance BiCMOS product designed for V_{CC} operation at 3.3 V.

This device is a 16-bit buffer and line driver featuring non-inverting 3-state bus outputs. The device can be used as four 4-bit buffers, two 8-bit buffers, or one 16-bit buffer.

2. Features and benefits

- 16-bit bus interface
- 3-state buffers
- Output capability: +64 mA and -32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Bus hold data inputs eliminate need for external pull-up resistors to hold unused inputs
- Power-up 3-state
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Latch-up protection
 - JESD78B Class II exceeds 500 mA
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V

3. Ordering information

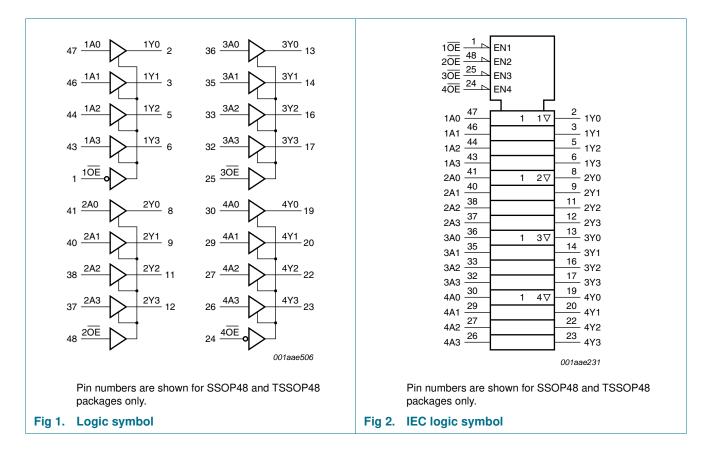
Table 1. Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74LVT16244BDL	–40 °C to +85 °C	SSOP48	plastic shrink small outline package; 48 leads;	SOT370-1				
74LVTH16244BDL			body width 7.5 mm					
74LVT16244BDGG	–40 °C to +85 °C	TSSOP48	plastic thin shrink small outline package;	SOT362-1				
74LVTH16244BDGG			48 leads; body width 6.1 mm					
74LVT16244BEV	–40 °C to +85 °C	VFBGA56	plastic very thin fine-pitch ball grid array package; 56 balls; body $4.5 \times 7 \times 0.65$ mm	SOT702-1				
74LVT16244BBQ	–40 °C to +85 °C		plastic thermal enhanced extremely thin quad	SOT1134-1				
74LVTH16244BBQ			flat package; no leads; 60 terminals; UTLP based; body $4 \times 6 \times 0.5$ mm					



3.3 V 16-bit buffer/driver; 3-state

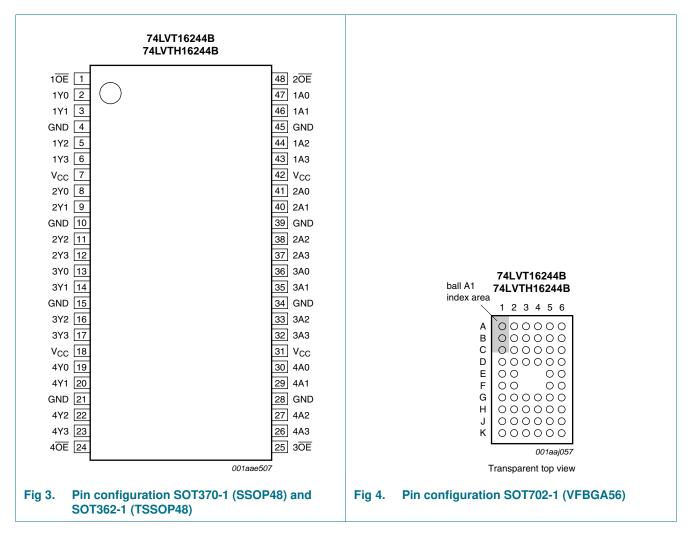
4. Functional diagram



3.3 V 16-bit buffer/driver; 3-state

5. Pinning information

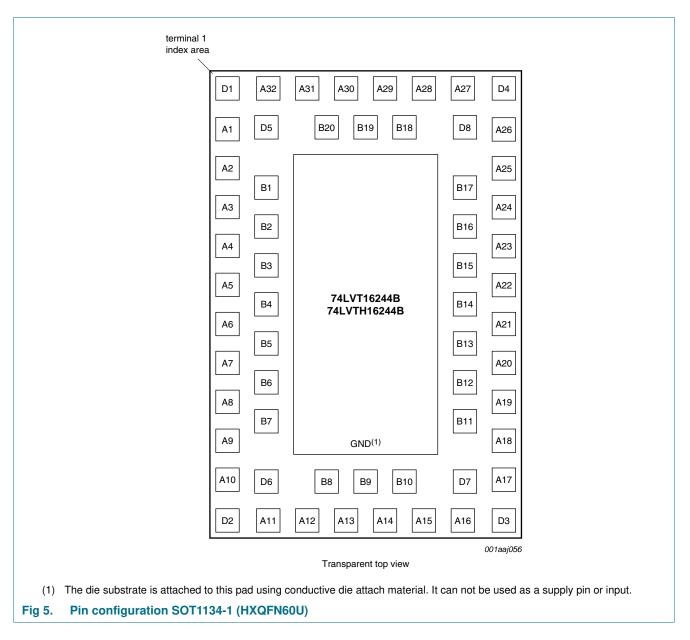
5.1 Pinning



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74LVT16244B; 74LVTH16244B

3.3 V 16-bit buffer/driver; 3-state



5.2 Pin description

Table 2. Pin description									
Symbol	Pin		Description						
	SOT370-1 and SOT362-1	SOT702-1	SOT1134-1						
1 <u>0E</u> , 2 <u>0E</u> , 30E, 40E	1, 48, 25, 24	A1, A6, K6, K1	A30, A29, A14, A13	output enable input (active LOW)					
1Y0 to 1Y3	2, 3, 5, 6	B2, B1, C2, C1	B20, A31, D5, D1	data output					
2Y0 to 2Y3	8, 9, 11, 12	D2, D1, E2, E1	A2, B2, B3, A5	data output					
3Y0 to 3Y3	13, 14, 16, 17	F1, F2, G1, G2	A6, B5, B6, A9	data output					
4Y0 to 4Y3	19, 20, 22, 23	H1, H2, J1, J2	D2, D6, A12, B8	data output					

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3.3 V 16-bit buffer/driver; 3-state

Symbol	Pin			Description
	SOT370-1 and SOT362-1	SOT702-1	SOT1134-1	_
GND	4, 10, 15, 21, 28, 34, 39, 45	B3, B4, D3, D4, G3, G4, J3, J4	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)
V _{CC}	7, 18, 31, 42	C3, C4, H3, H4	A1, A10, A17, A26	supply voltage
1A0 to 1A3	47, 46, 44, 43	B5, B6, C5, C6	B18, A28, D8, D4	data input
2A0 to 2A3	41, 40, 38, 37	D5, D6, E5, E6	A25, B16, B15, A22	data input
3A0 to 3A3	36, 35, 33, 32	F6, F5, G6, G5	A21, B13, B12, A18	data input
4A0 to 4A3	30, 29, 27, 26	H6, H5, J6, J5	D3, D7, A15, B10	data input
n.c.	-	A2, A3, A4, A5, K2, K3, K4, K5	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected

Table 2. Pin description ...continued

6. Functional description

Table 3. Function table ^[1]		
Control	Input	Output
nOE	nAn	nYn
L	L	L
L	Н	Н
Н	Х	Z

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
VI	input voltage		<u>[1]</u> –0.5	+7.0	V
Vo	output voltage	output in OFF-state or HIGH-state	<u>[1]</u> –0.5	+7.0	V
I _{IK}	input clamping current	V ₁ < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
lo	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-64	-	mA
T _{stg}	storage temperature		-65	+150	°C
T _i	junction temperature		[2]	150	°C

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +85 \ ^{\circ}C;$			
		(T)SSOP48 package	[3] _	500	mW
		VFBGA56 package	<u>[4]</u> _	1000	mW
		HXQFN60U package	<u>[4]</u> _	1000	mW

[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

[3] Above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

[4] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{CC}	supply voltage		2.7	-	3.6	V
VI	input voltage		0	-	5.5	V
V _{IH}	HIGH-level input voltage		2.0	-	-	V
V _{IL}	LOW-level input voltage		-	-	0.8	V
I _{OH}	HIGH-level output current		-32	-	-	mA
I _{OL}	LOW-level output current	none	-	-	32	mA
		$\begin{array}{l} \mbox{current duty cycle} \leq 50 \ \%; \\ f_i \geq 1 \ \mbox{kHz} \end{array}$	-	-	64	mA
T _{amb}	ambient temperature	in free-air	-40	-	+85	°C
$\Delta t / \Delta V$	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

3.3 V 16-bit buffer/driver; 3-state

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = -	40 °C to +85 °C <u>[1]</u>					
V _{IK}	input clamping voltage	V_{CC} = 2.7 V; I_{IK} = -18 mA	-1.2	-0.85	-	V
V _{OH}	HIGH-level output voltage	I_{OH} = $-100~\mu A;~V_{CC}$ = 2.7 V to 3.6 V	$V_{CC}-0.2$	V _{CC}	-	V
		$I_{OH} = -8 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.4	2.5	-	V
		$I_{OH} = -32 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	2.3	-	V
V _{OL}	LOW-level output voltage	$V_{CC} = 2.7 V$				
		I _{OL} = 100 μA	-	0.07	0.2	V
		I _{OL} = 24 mA	-	0.3	0.5	V
		$V_{CC} = 3.0 V$				
		I _{OL} = 16 mA	-	0.25	0.4	V
		I _{OL} = 32 mA	-	0.3	0.5	V
		I _{OL} = 64 mA	-	0.4	0.55	V
l _l	input leakage current	all input pins; V_{CC} = 0 V or 3.6 V; V_{I} = 5.5 V	-	0.1	10	μA
		control pins; V_{CC} = 3.6 V; V_I = V_{CC} or GND	-	0.1	±1.0	μA
		data pins; $V_{CC} = 3.6 V$	[2]			
		$V_{I} = V_{CC}$	-	0.1	1	μA
		$V_1 = 0 V$	-5	-0.1	-	μA
I _{OFF}	power-off leakage current	V_{CC} = 0 V; V _I or V _O = 0 V to 4.5 V	-	0.1	±100	μA
I _{BHL}	bus hold LOW current	$V_{CC} = 3 \text{ V}; \text{ V}_{I} = 0.8 \text{ V}$	<u>[3]</u> 75	135	-	μA
I _{BHH}	bus hold HIGH current	$V_{CC} = 3 \text{ V}; \text{ V}_{I} = 2.0 \text{ V}$	-	-135	-75	μA
I _{BHLO}	bus hold LOW overdrive current	nAn input; V_{CC} = 0 V to 3.6 V; V_{I} = 3.6 V	500	-	-	μA
I _{BHHO}	bus hold HIGH overdrive current	nAn input; V_{CC} = 0 V to 3.6 V; V_{I} = 3.6 V	-	-	-500	μA
I _{HOLD}	bus hold current data	$V_{CC} = 3 V$	[3]			
	input	V ₁ = 0.8 V	75	135	-	μA
		V ₁ = 2.0 V	-	-135	-75	μA
		V _{CC} = 0 V to 3.6 V				
		V ₁ = 3.6 V	±500	-	-	μA
I _{LO}	output leakage current	output in HIGH-state when V_O > V_CC; V_O = 5.5 V; V_CC = 3.0 V	-	50	125	μA
I _{O(pu/pd)}	power-up/power-down output current	$V_{CC} \leq \underline{1.2}~V;~V_{O}$ = 0.5 V to $V_{CC};~V_{I}$ = GND or $V_{CC};~n\overline{OE}$ = don't care	<u>[4]</u> _	1	±100	μA
l _{oz}	OFF-state output current	V_{CC} = 3.6 V; V_{I} = V_{IH} or V_{IL}				
		output HIGH: V _O = 3.0 V	-	0.5	5	μA
		output LOW: $V_O = 0.5 V$	-5	+0.5	-	μA

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I _{CC} supply current		V_{CC} = 3.6 V; V_{I} = GND or $V_{CC};I_{O}$ = 0 A				
	output HIGH	-	0.07	0.12	mA	
		output LOW	-	4.0	6.0	mA
		outputs disabled	[5] _	0.07	0.12	mA
ΔI_{CC}	additional supply current	per input pin; V_{CC} = 3.0 V to 3.6 V; one input at V_{CC} – 0.6 V other inputs at V_{CC} or GND	<u>[6]</u>	0.1	0.2	mA
CI	input capacitance	V _I = 0 V or 3.0 V	-	3	-	pF
Co	output capacitance	outputs disabled; $V_{\Omega} = 0 V \text{ or } 3.0 V$	-	9	-	рF

Table 6. Static characteristics ... continued

[1] Typical values are measured at V_{CC} = 3.3 V and at T_{amb} = 25 °C.

[2] Unused pins at V_{CC} or GND.

This is the bus hold overdrive current required to force the input to the opposite logic state. [3]

This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = $3.3 \text{ V} \pm 0.3 \text{ V}$ [4] a transition time of 100 μ s is permitted. This parameter is valid for T_{amb} = 25 °C only.

[5] I_{CC} is measured with outputs pulled to V_{CC} or GND.

[6] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

Table 7. **Dynamic characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

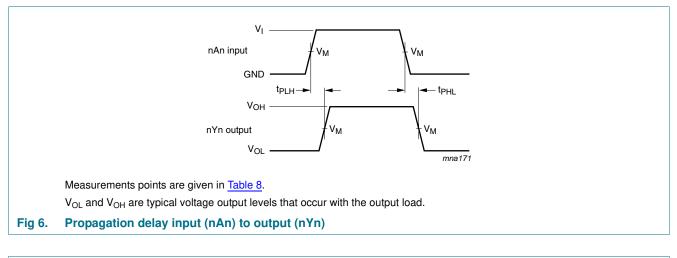
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
T _{amb} = -40	°C to +85 °C <u>[1]</u>					
t _{PLH}	LOW to HIGH	nAn to nYn; see <u>Figure 6</u>				
	propagation delay	$V_{CC} = 2.7 V$	-	-	4.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	0.5	1.8	3.2	ns
t _{PHL}	HIGH to LOW	nAn to nYn; see <u>Figure 6</u>				
	propagation delay	$V_{CC} = 2.7 V$	-	-	4.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	0.5	1.7	3.2	ns
t _{PZH}	OFF-state to HIGH propagation delay	nOE to nYn; see <u>Figure 7</u>				
		$V_{CC} = 2.7 V$	-	-	5.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	2.3	4.0	ns
t _{PZL}	OFF-state to LOW	nOE to nYn; see <u>Figure 7</u>				
	propagation delay	$V_{CC} = 2.7 V$	-	-	5.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	2.1	4.0	ns
t _{PHZ}	HIGH to OFF-state	nOE to nYn; see Figure 7				
	propagation delay	$V_{CC} = 2.7 V$	-	-	5.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	3.2	4.5	ns
t _{PLZ}	LOW to OFF-state	nOE to nYn; see <u>Figure 7</u>				
	propagation delay	V _{CC} = 2.7 V	-	-	4.4	ns
		$V_{CC} = 3.0 \text{ V}$ to 3.6 V	1.0	2.9	4.0	ns

[1] Typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

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3.3 V 16-bit buffer/driver; 3-state

11. Waveforms



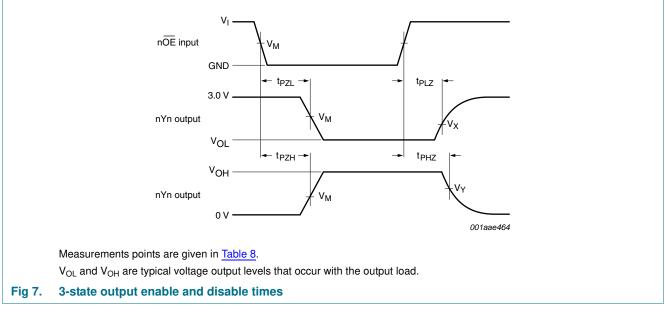


Table 8. Measurement points

Input	Output		
V _M	V _M	V _X	V _Y
1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V

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3.3 V 16-bit buffer/driver; 3-state

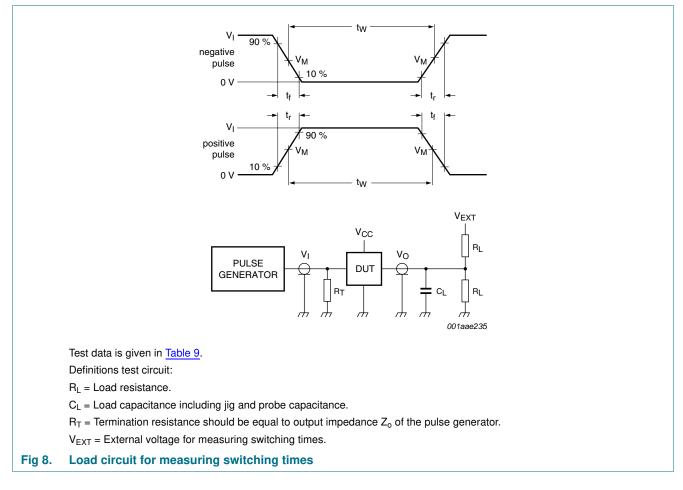


Table 9. Test data

Input			Load		V _{EXT}			
VI	f _i	tw	t _r , t _f	CL	RL	t _{PHZ} , t _{PZH}	t _{PLZ} , t _{PZL}	t _{PLH} , t _{PHL}
2.7 V	\leq 10 MHz	500 ns	\leq 2.5 ns	50 pF	500 Ω	GND	6 V	open

3.3 V 16-bit buffer/driver; 3-state

12. Package outline

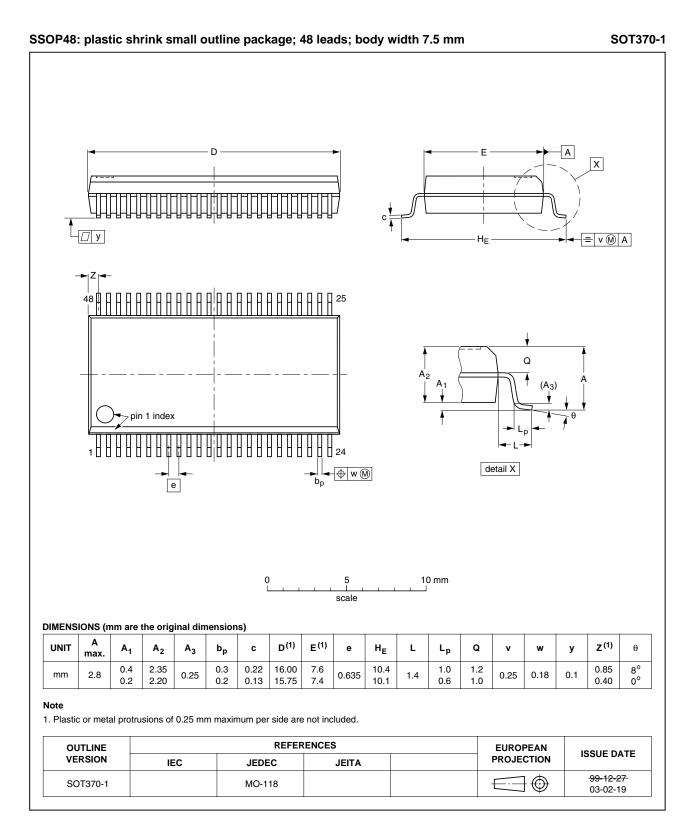


Fig 9. Package outline SOT370-1 (SSOP48)

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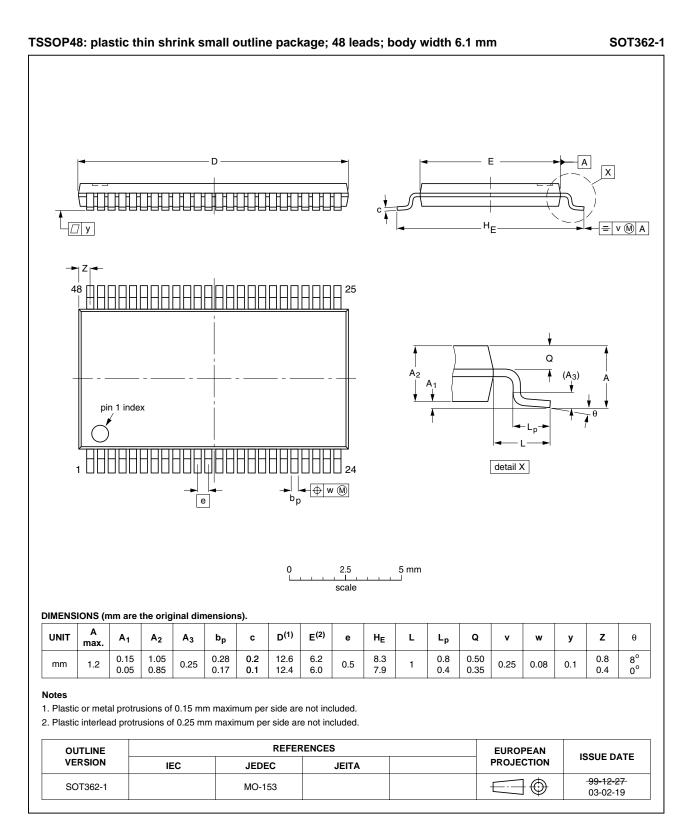
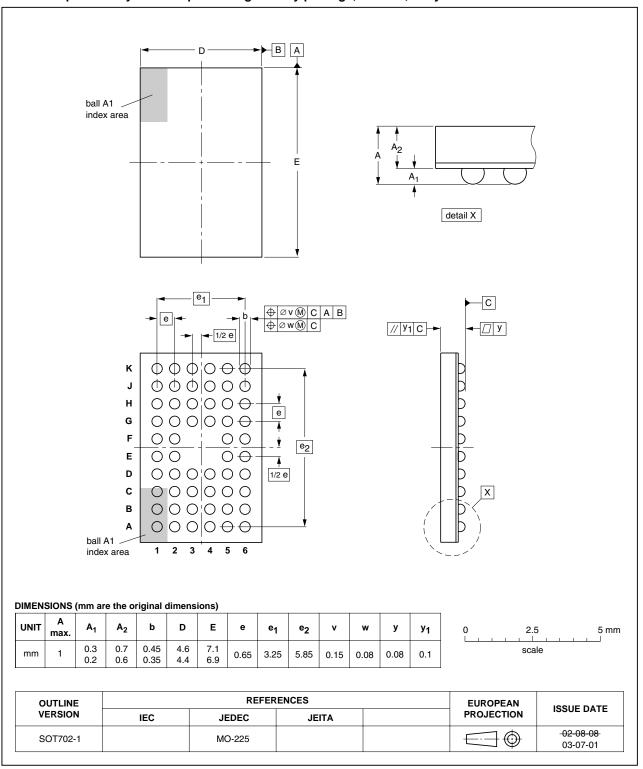


Fig 10. Package outline SOT362-1 (TSSOP48)

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3.3 V 16-bit buffer/driver; 3-state



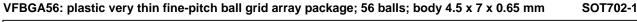
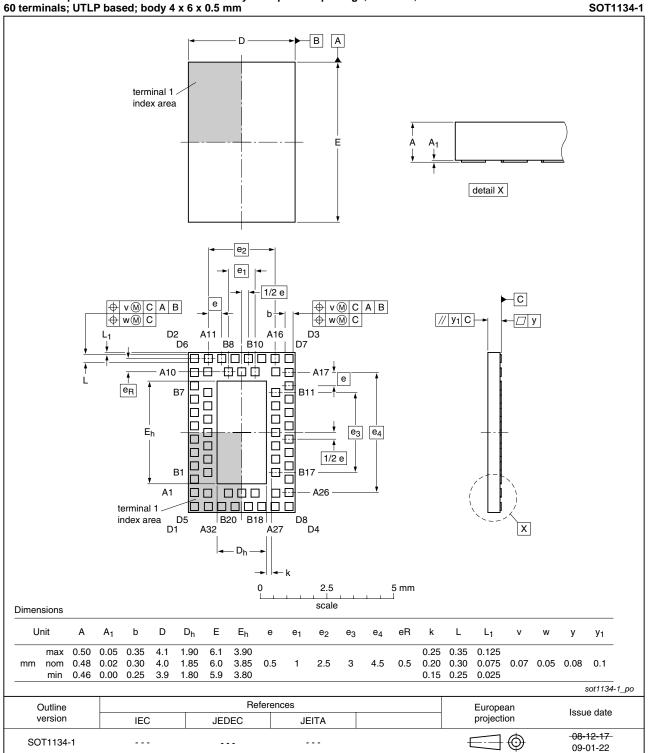


Fig 11. Package outline SOT702-1 (VFBGA56)

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3.3 V 16-bit buffer/driver; 3-state



HXQFN60U: plastic thermal enhanced extremely thin quad flat package; no leads; 60 terminals; UTLP based; body 4 x 6 x 0.5 mm

Fig 12. Package outline SOT1134-1 (HXQFN60U)

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3.3 V 16-bit buffer/driver; 3-state

13. Abbreviations

AcronymDescriptionBiCMOSBipolar Complementary Metal Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelTTLTransistor-Transistor Logic	Table 10.	Abbreviations	
DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	Acronym		Description
ESDElectroStatic DischargeHBMHuman Body ModelMMMachine Model	BiCMOS		Bipolar Complementary Metal Oxide Semiconductor
HBM Human Body Model MM Machine Model	DUT		Device Under Test
MM Machine Model	ESD		ElectroStatic Discharge
	HBM		Human Body Model
TTL Transistor-Transistor Logic	MM		Machine Model
	TTL		Transistor-Transistor Logic

14. Revision history

Table 11. Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes		
74LVT_LVTH16244B_8	20100322	Product data sheet	-	74LVT_LVTH16244B_7		
Modifications:		BBQ and 74LVTH16244BBQ ((SOT1134-1) package.	changed from HUQF	N60U (SOT1025-1) to		
74LVT_LVTH16244B_7	20090326	Product data sheet	-	74LVT_LVTH16244B_6		
74LVT_LVTH16244B_6	20081113	Product data sheet	-	74LVT_LVTH16244B_5		
74LVT_LVTH16244B_5	20060321	Product data sheet	-	74LVT16244B_4		
74LVT16244B_4	20021031	Product specification	-	74LVT16244B_3		
74LVT16244B_3	19981007	Product specification	-	74LVT16244B_2		
74LVT16244B_2	19980219	Product specification	-	-		

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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3.3 V 16-bit buffer/driver; 3-state

16. Contact information

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For sales office addresses, please send an email to: salesaddresses@nxp.com

3.3 V 16-bit buffer/driver; 3-state

17. Contents

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